

N-Channel Enhancement Mode Power MOSFET

Description

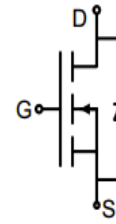
The G80N03K uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

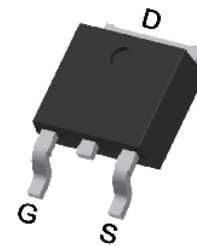
- V_{DS} 30V
- I_D (at $V_{GS} = 10V$) 80A
- $R_{DS(ON)}$ (at $V_{GS} = 10V$) < 6.5m Ω
- $R_{DS(ON)}$ (at $V_{GS} = 5V$) < 10m Ω
- 100% Avalanche Tested
- RoHS Compliant

Application

- Power switch
- DC/DC converters



Schematic diagram



TO-252

Device	Package	Marking	Packaging
G80N03K	TO-252	G80N03	2500pcs/Reel

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Continuous Drain Current	I_D	80	A
Pulsed Drain Current (note1)	I_{DM}	320	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	P_D	69	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	$^\circ\text{C}$

Thermal Resistance

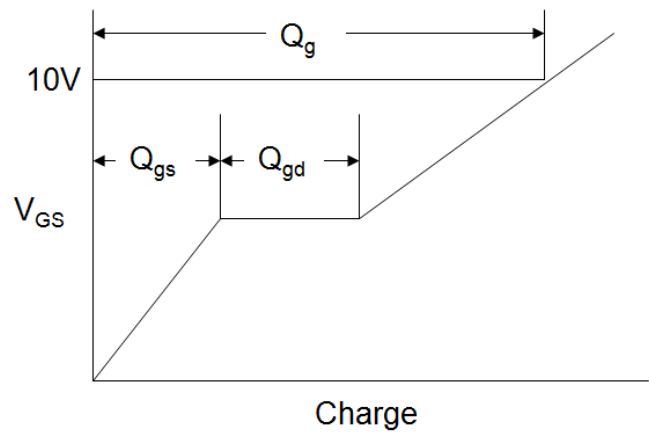
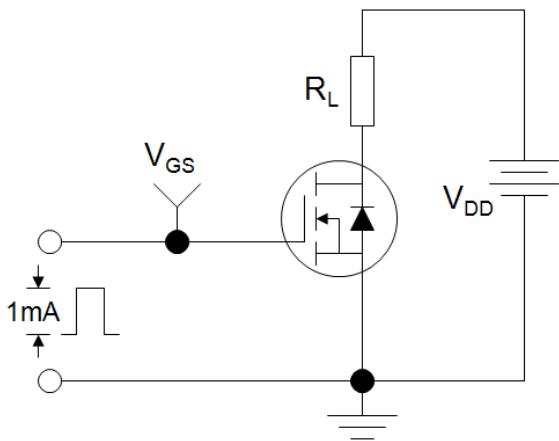
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	1.8	$^\circ\text{C/W}$

Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$	--	--	1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.6	2	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 25A$	--	3.5	6.5	m Ω
		$V_{GS} = 4.5V, I_D = 25A$	--	5	10	
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=15A$	--	28	--	S
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 15V,$ $f = 1.0\text{MHz}$	--	1950	--	pF
Output Capacitance	C_{oss}		--	320	--	
Reverse Transfer Capacitance	C_{rss}		--	240	--	
Total Gate Charge	Q_g	$V_{DD} = 25V,$ $I_D = 20A,$ $V_{GS} = 10V$	--	42	--	nC
Gate-Source Charge	Q_{gs}		--	4	--	
Gate-Drain Charge	Q_{gd}		--	14	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 15V,$ $I_D = 20A,$ $R_G = 3\Omega$	--	13	--	ns
Turn-on Rise Time	t_r		--	36	--	
Turn-off Delay Time	$t_{d(off)}$		--	43	--	
Turn-off Fall Time	t_f		--	16	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	80	A
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = 25A, V_{GS} = 0V$	--	--	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F=20A, di/dt=100A/\mu s$	--	16	--	ns
Body Diode Reverse Recovery Charge	Q_{rr}		--	5	--	nc

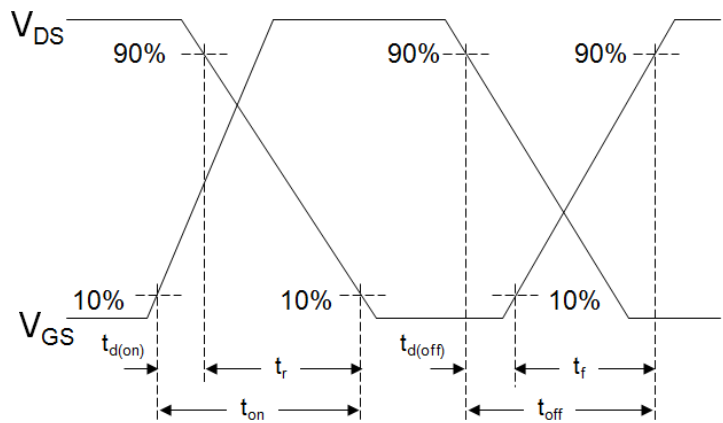
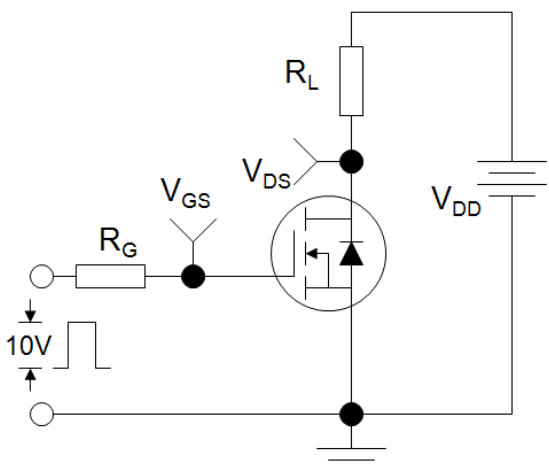
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical R_G

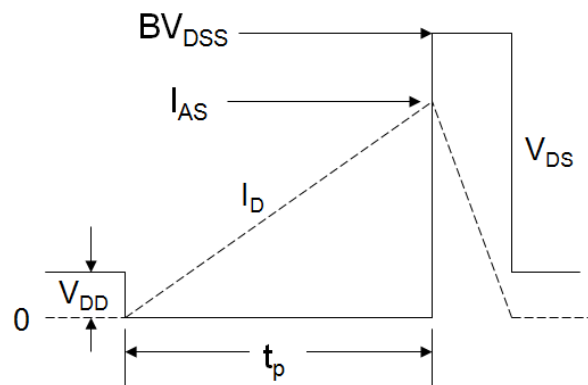
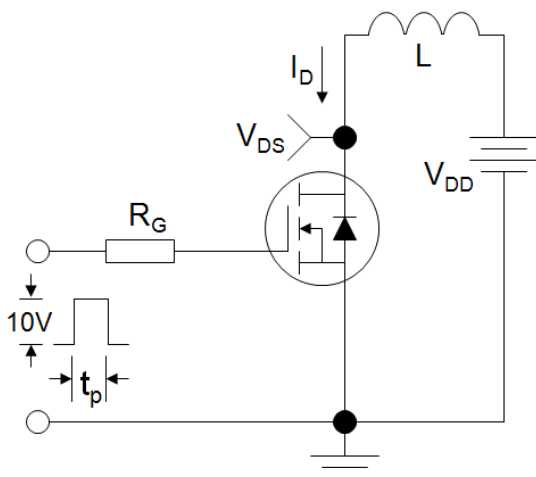
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

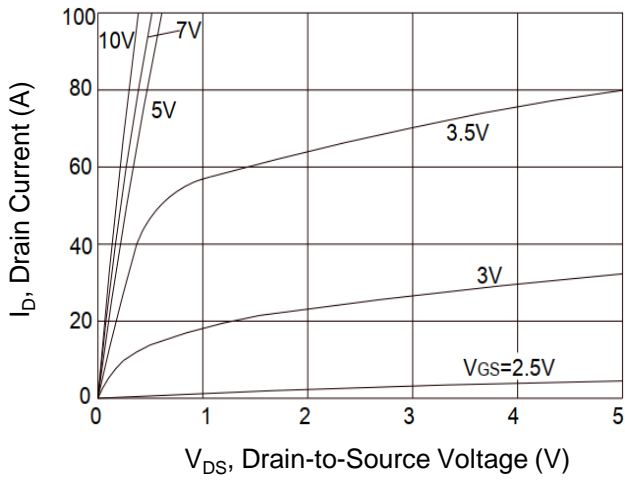


Figure 2. Transfer Characteristics

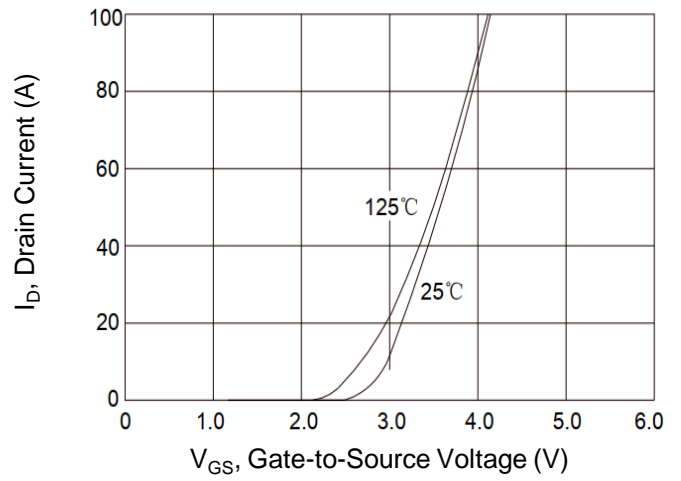


Figure 3. Gate Charge

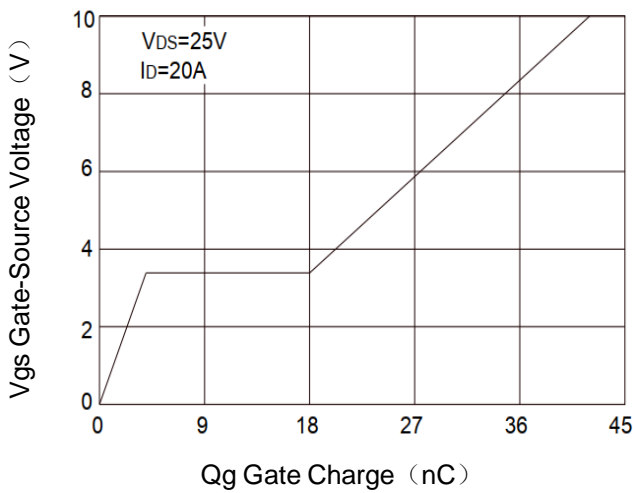


Figure 4. Drain Source On Resistance

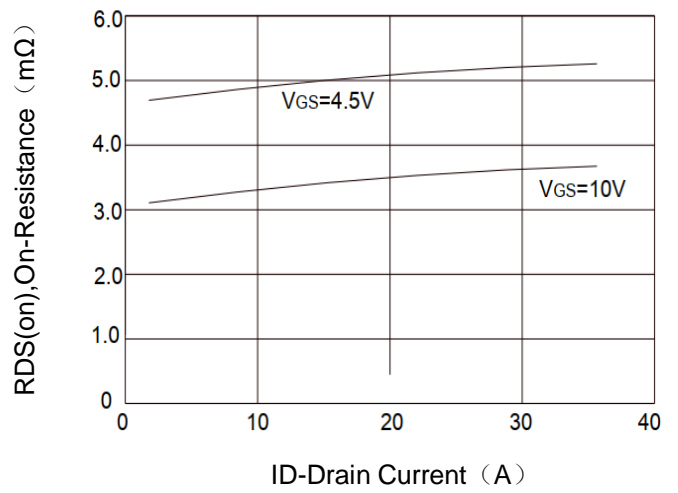


Figure 5. Capacitance

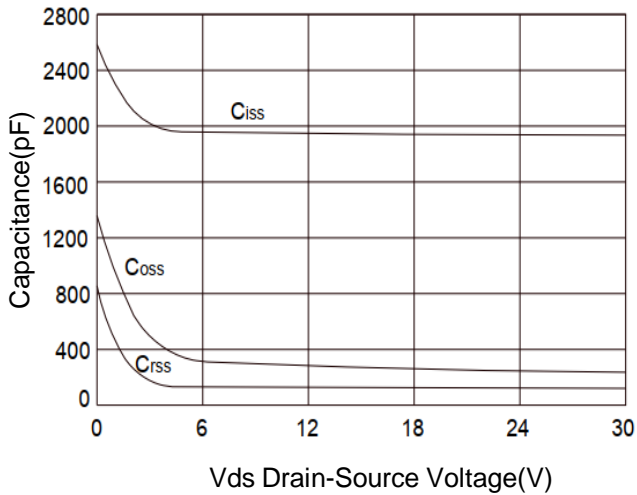
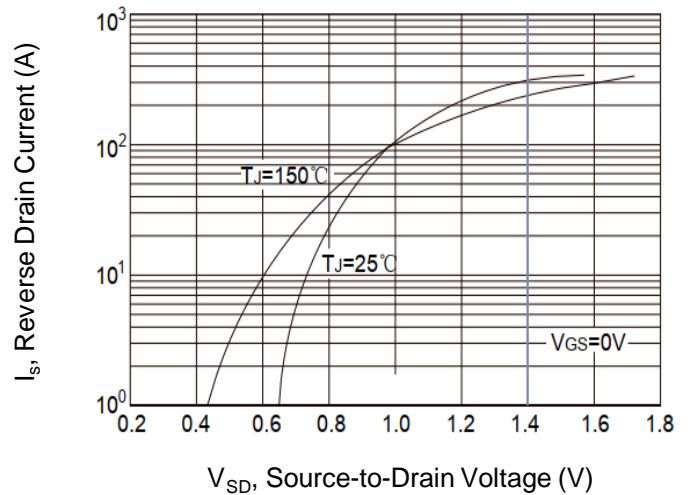


Figure 6. Source-Drain Diode Forward



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Figure 7. Drain-Source On-Resistance

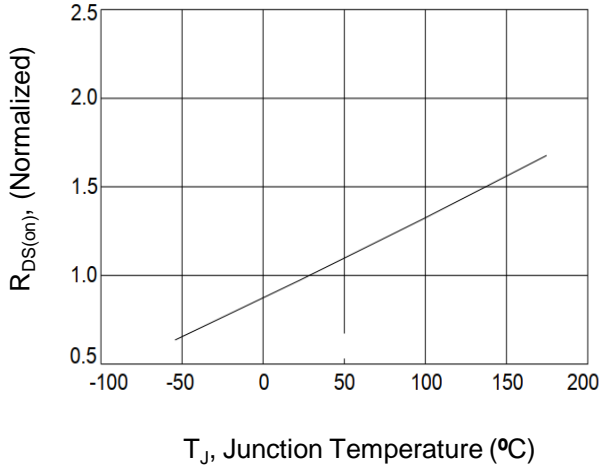


Figure 8. Safe Operation Area

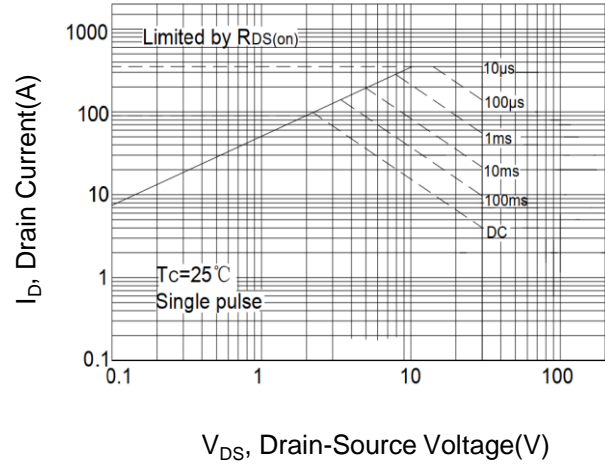
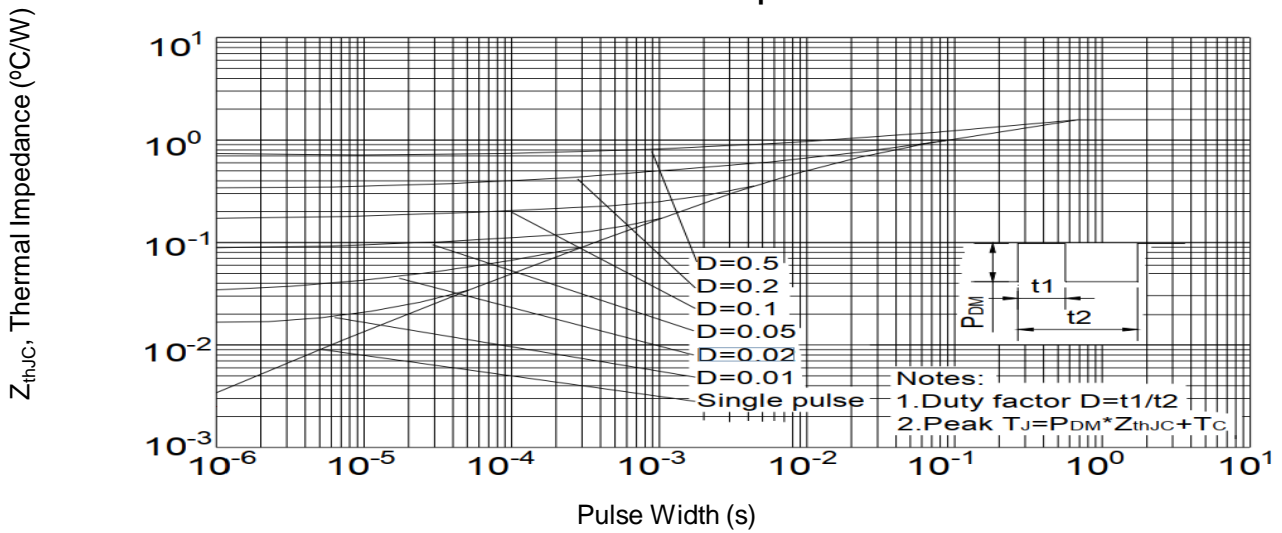
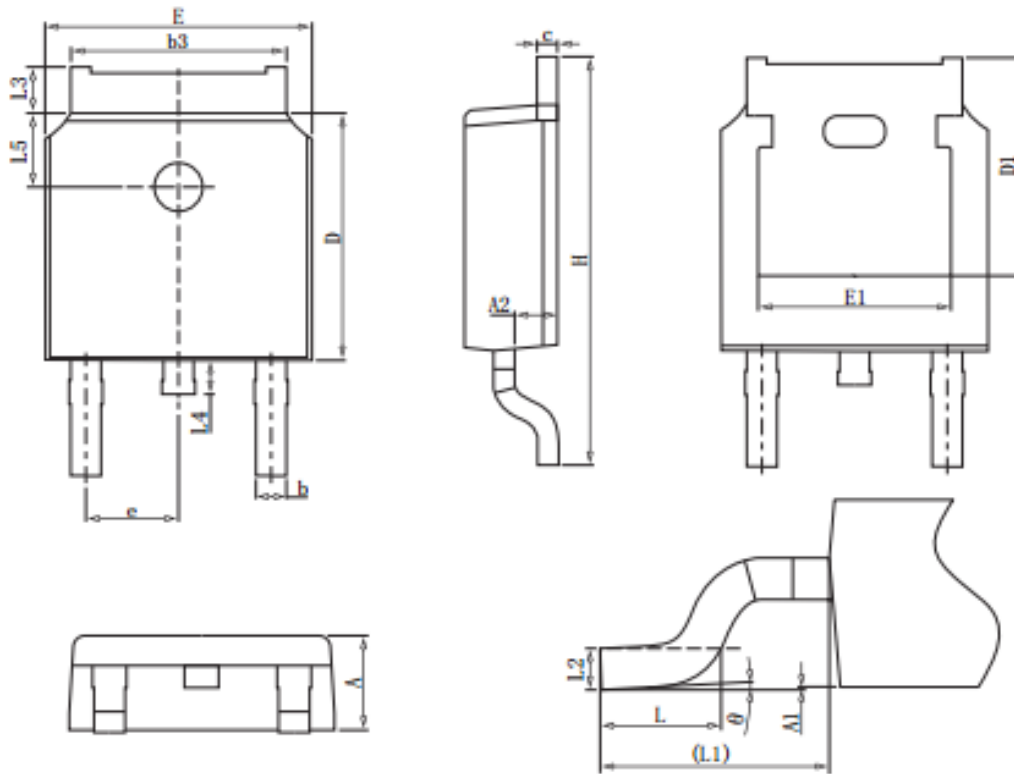


Figure 9. Normalized Maximum Transient Thermal Impedance



TO-252 Package Information



Symbol	Dimensions in Millimeters		
	MIN.	NOM.	MAX.
A	2.2	2.3	2.4
A1	0		0.2
A2	0.97	1.07	1.17
b	0.68	0.78	0.9
b3	5.2	5.33	5.5
c	0.43	0.53	0.63
D	5.98	6.1	6.22
D1	5.30REF		
E	6.4	6.6	6.8
E1	4.63		
e	2.286BSC		
H	9.4	10.1	10.5
L	1.38	1.5	1.75
L1	2.90REF		
L2	0.51BSC		
L3	0.88		1.28
L4	0.5		1
L5	1.65	1.8	1.95
θ	0°		8°